MMBD202CAW

SILICON EPITAXIAL PLANAR SWITCHING DIODE

Application

• Ultra high speed switching





SOT-323 Plastic Package Marking Code: YX

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Forward Current (Single)	Io	100	mA
Maximum Peak Forward Current (Single)	I _{FM}	300	mA
Surge Current at t = 1 µs (Single)	I _{FSM}	4	А
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

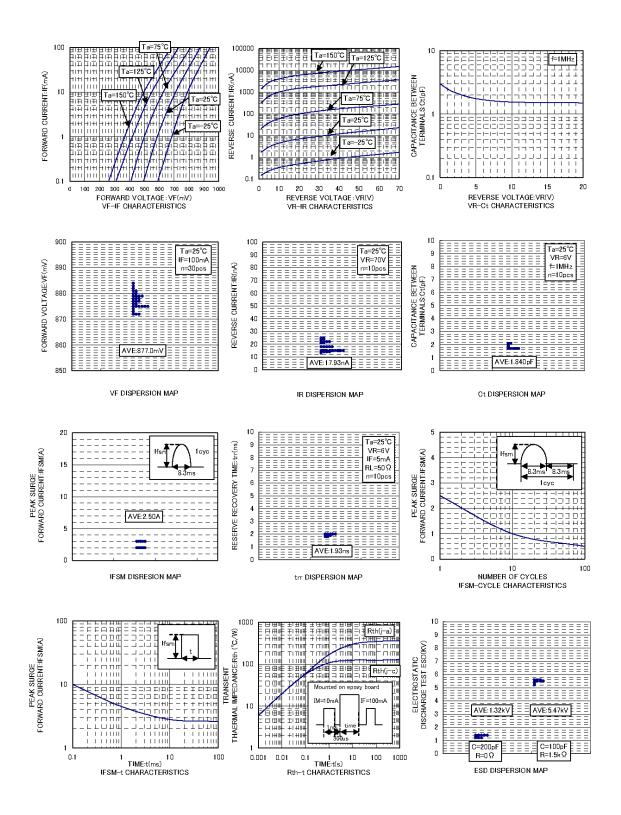
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 70 \text{ V}$	I _R	0.1	μΑ
Capacitance Between Terminals at $V_R = 6 \text{ V}$, $f = 1 \text{ MHz}$	Ст	3.5	pF
Reverse Recovery Time at V_R = 6 V, I_F = 5 mA, R_L = 50 Ω	t _{rr}	4	ns







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